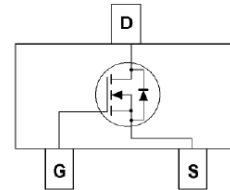


N-Channel Enhancement Mode MOSFET

Feature

- 30V/1A, $R_{DS(ON)} = 750\text{m}\Omega$ (MAX) @ $V_{GS} = 10\text{V}$, $I_{DS} = 0.60\text{A}$
 $R_{DS(ON)} = 900\text{m}\Omega$ (MAX) @ $V_{GS} = 4.5\text{V}$, $I_{DS} = 0.20\text{A}$
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- SOT-23 for Surface Mount Package.



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ Unless Otherwise noted

| Parameter | Symbol | Limit | Units |
|--------------------------|----------|----------|-------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 1 | A |

Electrical Characteristics $T_A=25^\circ\text{C}$ Unless Otherwise noted

| Parameter | Symbol | Test Conditions | Min | Typ. | Max | Units |
|---|--------------|---|-----|------|------|------------------|
| Off Characteristics | | | | | | |
| Drain to Source Breakdown Voltage | BVDSS | $V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$ | 30 | - | - | V |
| Zero-Gate Voltage Drain Current | I_{DSS} | $V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ | - | - | 1 | μA |
| Gate Body Leakage Current, Forward | I_{GSSF} | $V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$ | - | - | 100 | nA |
| Gate Body Leakage Current, Reverse | I_{GSSR} | $V_{GS}=-20\text{V}$, $V_{DS}=0\text{V}$ | - | - | -100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$ | 1 | - | - | V |
| Static Drain-source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=10\text{V}$, $I_D=0.6\text{A}$ | - | - | 750 | $\text{m}\Omega$ |
| | | $V_{GS}=4.5\text{V}$, $I_D=0.2\text{A}$ | - | - | 900 | $\text{m}\Omega$ |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| Drain-Source Diode Forward Voltage | VSD | $V_{GS}=0\text{V}$, $I_S=0.23\text{A}$ | | | 1.2 | V |